

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1
 Stylesheet Version v1.2

EPAS ID: PAT7039509

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	SECURITY INTEREST
SEQUENCE:	2

CONVEYING PARTY DATA

Name	Execution Date
RAJE TECHNOLOGY GROUP, LLC	11/08/2021
PLASMA-THERM, LLC	11/08/2021
REV-TECH MANUFACTURING SOLUTIONS, LLC	11/08/2021
PLASMA-THERM NES, LLC	11/08/2021

RECEIVING PARTY DATA

Name:	HSBC BANK USA, N.A.
Street Address:	2929 WALDEN AVENUE
Internal Address:	LOCATION C-112
City:	DEPEW
State/Country:	NEW YORK
Postal Code:	14043

PROPERTY NUMBERS Total: 56

Property Type	Number
Patent Number:	6771482
Patent Number:	6846747
Patent Number:	6905626
Patent Number:	6924235
Patent Number:	6982175
Patent Number:	7115520
Patent Number:	7008877
Patent Number:	7101805
Patent Number:	7959819
Patent Number:	7713432
Patent Number:	7625824
Patent Number:	7381650
Patent Number:	7833381
Patent Number:	7749400
Patent Number:	7867403

PATENT

Property Type	Number
Patent Number:	7829465
Patent Number:	8187483
Patent Number:	8139340
Patent Number:	8802545
Patent Number:	8778806
Patent Number:	9368404
Patent Number:	10497621
Patent Number:	8796154
Patent Number:	8785332
Patent Number:	10707060
Patent Number:	8980764
Patent Number:	9202720
Patent Number:	10297427
Patent Number:	9564366
Patent Number:	8946058
Patent Number:	RE46339
Patent Number:	9070760
Patent Number:	9496177
Patent Number:	9105705
Patent Number:	10573557
Patent Number:	8691702
Patent Number:	9343365
Patent Number:	9202721
Patent Number:	9082839
Patent Number:	9202737
Patent Number:	11075057
Patent Number:	10269641
Patent Number:	10818552
Patent Number:	9865436
Patent Number:	9863036
Patent Number:	8703001
Patent Number:	9911654
Patent Number:	10741447
Patent Number:	9711406
Patent Number:	10943825
Patent Number:	10246781
Patent Number:	11114340
Patent Number:	10767257

Property Type	Number
Patent Number:	8967081
Patent Number:	9777374
Patent Number:	6544696

CORRESPONDENCE DATA

Fax Number:

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

Phone: 2026637271

Email: thomas.brooke@hklaw.com

Correspondent Name: THOMAS W. BROOKE

Address Line 1: C/O HOLLAND & KNIGHT LLP, 800 17TH ST NW

Address Line 2: SUITE 1100

Address Line 4: WASHINGTON, D.C. 20006

NAME OF SUBMITTER:	THOMAS W. BROOKE
SIGNATURE:	/Thomas W. Brooke/
DATE SIGNED:	11/23/2021
	This document serves as an Oath/Declaration (37 CFR 1.63).

Total Attachments: 12

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**SECOND AMENDED AND RESTATED
INTELLECTUAL PROPERTY SECURITY AGREEMENT**
(Domestic Credit Facilities)

This SECOND AMENDED AND RESTATED INTELLECTUAL PROPERTY SECURITY AGREEMENT, dated as of November 8, 2021 (as amended, supplemented or otherwise modified from time to time, this “Intellectual Property Security Agreement”), is made by RAJE Technology Group, LLC, a Florida limited liability company (“RAJE”), Plasma-Therm, LLC, a Florida limited liability company (“Plasma”), Rev-Tech Manufacturing Solutions, LLC, a Florida limited liability company (“Rev-Tech”), and Plasma-Therm NES, LLC, a Florida limited liability company (“Plasma NES”)(RAJE, Plasma, Rev-Tech and Plasma NES are sometimes each hereafter referred to as a “Grantor” and collectively, the “Grantors”) in favor of HSBC Bank USA, N.A., a national banking association (the “Lender”).

RECITALS

WHEREAS, RAJE, Plasma, Rev-Tech, and Hine Automation, LLC, a Delaware limited liability company (“Hine”) (RAJE, Plasma, Rev-Tech, and Hine are sometimes referred to herein as each, a “Borrower” and collectively, the “Borrowers”) have entered into that certain Loan and Security Agreement (Domestic Credit Facilities), dated as of November 21, 2018 (the “Original Loan and Security Agreement”), as amended by that certain First Amendment to Loan and Security Agreement (Domestic Credit Facilities), dated as of April 27, 2020 (the “First Amendment”), and as amended by that certain Second Amendment to Loan and Security Agreement (Domestic Credit Facilities), dated as of even date herewith (the “Second Amendment” and together with the Original Loan and Security Agreement and the First Amendment, as amended, restated, supplemented or otherwise modified from time to time, the “Loan and Security Agreement”), by and among the Borrowers and the Lender. Capitalized terms used and not defined herein have the meanings given such terms in the Loan and Security Agreement.

WHEREAS, each Borrower pursuant to the terms and conditions of the Loan and Security Agreement has granted a security interest in all General Intangibles of such Borrower, including, but not limited to, all Intellectual Property (as defined below) for the benefit of the Lender.

WHEREAS, Plasma NES, Drytek, LLC, a Delaware limited liability company (“Drytek”), Logix Technology Holdings, LLC, a Delaware limited liability company (“Logix”), and Plasma-Therm IC-DISC, Inc., a Delaware corporation (“Plasma IC-DISC”)(Plasma NES, Drytek, Logix, and Plasma IC-DISC are sometimes referred to herein as each, a “Guarantor” and collectively, the “Guarantors”) have entered into that certain Security Agreement (Domestic Credit Facilities), dated as of November 21, 2018 (as amended, restated, supplemented or otherwise modified from time to time, the “Security Agreement”), by and among the Guarantors and the Lender, to secure the prompt payment and performance of any and all obligations of the Borrowers.

WHEREAS, each Guarantor pursuant to the terms and conditions of the Security Agreement has granted a security interest in all General Intangibles (as defined in the Security Agreement) of such Guarantor, including, but not limited to, all Intellectual Property (as defined below) for the benefit of the Lender.

WHEREAS, it was a condition precedent to the obligation of the Lender to make its extension of credit to the Borrowers under the Original Loan and Security Agreement that the Grantors shall have each executed and delivered to and for the benefit of the Lender (i) the Original Loan and Security Agreement in the case of the Borrowers, and (ii) the Security Agreement in the case of the Guarantors (collectively, and together with the Loan and Security Agreement, the “Security Agreements”).

WHEREAS, under the terms of the Security Agreements, each Borrower and Guarantor has granted a security interest in certain Intellectual Property (as defined below) of such grantor to and for the benefit of the Lender and has agreed as a condition thereof to execute an Intellectual Property Security Agreement for recording with the United States Patent and Trademark Office, the United States Copyright Office, and any other applicable Governmental Authority.

WHEREAS, in connection with the Security Agreements, the Grantors executed and delivered to and for the benefit of the Lender a certain Intellectual Property Security Agreement, dated as of November 21, 2018 (the "Original IPSA"), which was filed (i) with respect to patents, in the United States Patent and Trademark Office, on November 30, 2018, at Reel 047688, Frame 0061 and (ii) with respect to trademarks in the United States Patent and Trademark Office, on November 26, 2018, at Reel 6555, Frame 0376.

WHEREAS, Plasma was issued patents in addition to the ones reflected in the Original IPSA.

WHEREAS, in connection with the First Amendment, the Grantors executed and delivered to and for the benefit of the Lender a certain Amended and Restated Intellectual Property Security Agreement (Domestic Credit Facilities), dated as of April 27, 2020 (the "A&R IPSA"), to update Schedule 1 to reflect such additional patents, which was filed with respect to patents, in the United States Patent and Trademark Office, on May 15, 2020, at Reel 052679, Frame 0788.

WHEREAS, Plasma was issued patents in addition to the ones reflected in the A&R IPSA.

WHEREAS, in connection with the Second Amendment, and as a condition precedent thereof, the Grantors and the Lender desire to amend and restate the A&R IPSA to further update Schedule 1 to reflect such additional patents.

NOW, THEREFORE, for good and valuable consideration, the receipt and sufficiency of which are hereby acknowledged, the Grantors agree as follows:

SECTION 1. Grant of Security. Each Grantor hereby grants to the Lender a security interest in and to all of such Grantor's right, title and interest in and to the following (the "Intellectual Property Collateral"), whether now existing or hereafter arising, as collateral security for the prompt and complete payment and performance when due (whether at the stated maturity, by acceleration or otherwise) of the Obligations:

(a) (i) all trademarks, service marks, trade names, corporate names, company names, business names, fictitious business names, trade dress, trade styles, logos, or other indicia of origin or source identification, trademark and service mark registrations, and applications for trademark or service mark registrations and any new renewals thereof, including, without limitation, each registration and application identified in Schedule 1, (ii) the right to sue or otherwise recover for any and all past, present and future infringements and misappropriations thereof, (iii) all income, royalties, damages and other payments now and hereafter due and/or payable with respect thereto (including, without limitation, payments under all licenses entered into in connection therewith, and damages and payments for past, present or future infringements thereof), and (iv) all other rights of any kind whatsoever of such Grantor accruing thereunder or pertaining thereto, together in each case with the goodwill of the business connected with the use of, and symbolized by, each of the above (collectively, the "Pledged Trademarks");

(b) (i) all patents, patent applications and patentable inventions, including, without limitation, each issued patent and patent application identified in Schedule 1, (ii) all inventions and

improvements described and claimed therein, (iii) the right to sue or otherwise recover for any and all past, present and future infringements and misappropriations thereof, (iv) all income, royalties, damages and other payments now and hereafter due and/or payable with respect thereto and in connection with clause (v) below (including, without limitation, payments under all licenses entered into in connection therewith, and damages and payments for past, present or future infringements thereof), and (v) all reissues, divisions, continuations, continuations-in-part, substitutes, renewals, and extensions thereof, all improvements thereon and all other rights of any kind whatsoever of such Grantor accruing thereunder or pertaining thereto (collectively, the “Pledged Patents”);

(c) (i) all copyrights, whether registered or unregistered and whether or not the underlying works of authorship have been published, and all works of authorship and other intellectual property rights therein (including, but not limited to, business software), all copyrights of works based on, incorporated in, derived from or relating to works covered by such copyrights, all right, title and interest to make and exploit all derivative works based on or adopted from works covered by such copyrights, and all copyright registrations and copyright applications, and any renewals or extensions thereof, including, without limitation, each registration and application identified in Schedule 1, (ii) the rights to print, publish and distribute any of the foregoing, (iii) the right to sue or otherwise recover for any and all past, present and future infringements and misappropriations thereof, (iv) all income, royalties, damages and other payments now and hereafter due and/or payable with respect thereto (including, without limitation, payments under all licenses entered into in connection therewith, and damages and payments for past, present or future infringements thereof), and (v) all other rights of any kind whatsoever of such Grantor accruing thereunder or pertaining thereto (collectively, “Pledged Copyrights”);

(d) (i) all trade secrets and all confidential and proprietary information, including know-how, manufacturing and production processes and techniques, inventions, research and development information, technical data, financial, marketing and business data, pricing and cost information, business and marketing plans, and customer and supplier lists and information, (ii) the right to sue or otherwise recover for any and all past, present and future infringements and misappropriations thereof, (iii) all income, royalties, damages and other payments now and hereafter due and/or payable with respect thereto (including, without limitation, payments under all licenses entered into in connection therewith, and damages and payments for past, present or future infringements thereof), and (iv) all other rights of any kind whatsoever of such Grantor accruing thereunder or pertaining thereto (collectively, the “Pledged Trade Secrets”);

(e) (i) all licenses or agreements, whether written or oral, providing for the grant by or to any Grantor of: (A) any right to use any Pledged Trademark or Pledged Trade Secret, (B) any right under any Pledged Patent, and (C) any right under any Pledged Copyright, (ii) the right to sue or otherwise recover for any and all past, present and future infringements and misappropriations of any of the foregoing, (iii) all income, royalties, damages and other payments now and hereafter due and/or payable with respect thereto (including, without limitation, payments under all licenses entered into in connection therewith, and damages and payments for past, present or future infringements thereof), and (iv) all other rights of any kind whatsoever of such Grantor accruing thereunder or pertaining thereto; and

(f) any and all proceeds of the foregoing.

SECTION 2. Recordation. Each Grantor authorizes and requests that the Register of Copyrights, the Commissioner of Patents and Trademarks and any other applicable government officer record this Intellectual Property Security Agreement.

SECTION 3. Execution in Counterparts. This Intellectual Property Security Agreement may be executed in any number of counterparts as necessary or convenient and by the different parties on

separate counterparts (including by electronic transmission), each of which when so executed shall be deemed to be an original and all of which taken together shall constitute one and the same agreement. Delivery of an executed counterpart of this Amendment (or of any agreement or document required by this Intellectual Property Security Agreement) by telecopy or other electronic imaging means (including, but not limited to, .PDF via email) shall be as effective, valid and legally binding as delivery of a manually executed counterpart of this Intellectual Property Security Agreement; provided, however, that the telecopy or other electronic image shall be promptly followed by an original if required by the Lender.

SECTION 4. Governing Law. This Intellectual Property Security Agreement shall be governed by, and construed and interpreted in accordance with the laws of the State of Florida. Without limiting the applicability of any other provision of the Loan and Security Agreement, the terms of Section 11.1 (*Governing Law; Choice of Forum; Service of Process; Jury Trial Waiver*) of the Loan and Security Agreement in the case of the Borrowers, and Section 9.9 (*Governing Law*) and Section 9.10 (*Submission to Jurisdiction; Waiver of Jury Trial*) in the Security Agreement in the case of the Guarantors, are incorporated herein, *mutatis mutandis*, and shall apply to and govern this Intellectual Property Security Agreement.

SECTION 5. Conflict Provision. This Intellectual Property Security Agreement has been entered into in conjunction with the provisions of the Security Agreements. The rights and remedies of each party hereto with respect to the security interest granted herein are without prejudice to, and are in addition to those set forth in the Security Agreements, all terms and provisions of which are incorporated herein by reference. In the event that any provisions of this Intellectual Property Security Agreement are in conflict with any Security Agreement, the provisions of such Security Agreement shall govern.

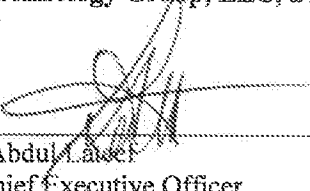
SECTION 6. Amendment and Restatement. This Intellectual Property Security Agreement amends and restates the A&R IPSA.

[Signature page follows]

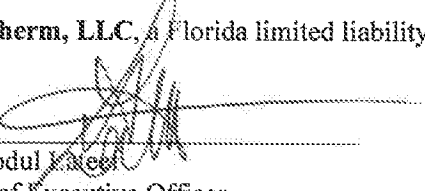
IN WITNESS WHEREOF, each of the undersigned has caused this Second Amended and Restated Intellectual Property Security Agreement to be duly executed and delivered as of the date first above written.

"GRANTORS"

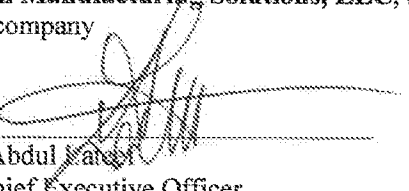
RAJE Technology Group, LLC, a Florida limited liability company

By: 
Name: Abdul Latif
Title: Chief Executive Officer

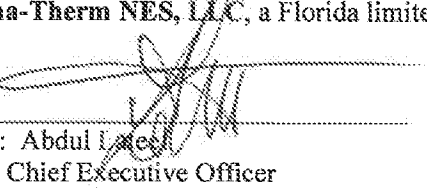
Plasma-Therm, LLC, a Florida limited liability company

By: 
Name: Abdul Latif
Title: Chief Executive Officer

Rev-Tech Manufacturing Solutions, LLC, a Florida limited liability company

By: 
Name: Abdul Latif
Title: Chief Executive Officer

Plasma-Therm NES, LLC, a Florida limited liability company

By: 
Name: Abdul Latif
Title: Chief Executive Officer

Schedule 1

[See attached]

List of United States Patents

Registered Owner: Plasma-Therm, LLC

Title or Parties	Inventors	Issue Date Issue No.
Perimeter seal for backside cooling	Kenney	8/3/2004 6,771,482
Method for Etching Vias	Westerman Johnson	1/25/2005 6,846,747
Notch-free Etching of High Aspect SOI structures using Alternating Deposition and Etching and Pulsed ICP	Westerman Johnson Lai	6/14/2005 6,905,626
Sidewall smoothing in high aspect ratio/deep etching using a discrete gas switching method	Westerman Johnson Lai	8/2/2005 6,924,235
End Point Detection in Time Division Multiplexed Etch Processes	Westerman Johnson	1/3/2006 6,982,175
A Method and Apparatus for Process Control in Time Division Multiplexed (TDM) Etch Processes	Westerman Johnson Lai	10/3/2006 7,115,520
Etching of Chromium Layers on Photomasks Utilizing High Density Plasma and Low Frequency RF Bias	Constantine Plumhoff Johnson Westerman	3/7/2006 7,008,877
Envelope Follower End Point Detection in Time Division Multiplexed Processes	Johnson Westerman	09/05/2006 7,101,805
A Method and Apparatus for Reducing Aspect Ratio Dependent Etching in TDM Etch Processes	Westerman Johnson Lai	06/14/2011 7,959,819
Method and Apparatus to Improve Plasma Etch Uniformity	Westerman Johnson	05/11/2010 7,713,432
Method for Process Change Detection	Plumhoff	12/1/2009 7,625,824
CIP of (PT-24) A Method and Apparatus for Process Control in Time Division Multiplexed (TDM) Etch Processes	Westerman Johnson Lai Teixeira	6/3/2008 7,381,650
Optical Emission Interferometry for PECVD using a Gas Injection Hole	Johnson	11/16/2010 7,833,381
Improved Method for Etching Photolithographic Substrates	Plumhoff	07/06/2010 7,749,400
Temperature Control Method for Photolithographic Substrate	Plumhoff Ryan Nolan Johnson Westerman	01/11/2011 7,867,403

A Method and Apparatus for Plasma Etching of Positively Sloped Structures	Lai Mackenzie Johnson	11/09/2010 7,829,465
Method to Minimize CD Etch Bias	Plumhoff Srinivasan Johnson Westerman	05/29/2012 8,187,483
Conductive Seal Ring Electrostatic Chuck	Reynolds	03/20/2012 8,139,340
Method and Apparatus for Plasma Dicing a Semi-conductor Wafer (2 step process)	CW Johnson DJ Johnson Pays-Volard Martinez Westerman Grivna	08/12/2014 8,802,545
DIV of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer (Dicing on Tape)	CW Johnson DJ Johnson Pays-Volard Martinez Westerman Grivna	07/15/2014 8,778,806
Method for Dicing a Substrate with Back Metal (Water Jet)	Falvo Martinez Pays-Volard Gauldin Westerman	06/14/2016 9,368,404
DIV of (PT-194) Method for Dicing a Substrate with Back Metal (Water Jet)	Falvo Martinez Pays-Volard Gauldin Westerman	12/03/2019 10,497,621
DIV of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Cover Ring	CW Johnson DJ Johnson Pays-Volard Martinez Westerman Grivna	08/05/2014 8,796,154
DIV of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Lift Mechanism	CW Johnson DJ Johnson Martinez Pays-Volard Rich Gauldin Westerman Grivna	07/22/2014 8,785,332

DIV of (PT-196) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Lift Mechanism	CW Johnson DJ Johnson Martinez Pays-Volard Rich Gauldin Westerman Grivna	07/07/2020 10,707,060
DIV of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - ICP Screen	Martinez Pays-Volard CW Johnson DJ Johnson Westerman Grivna	03/17/2015 8,980,764
DIV of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - ESC	Martinez Pays-Volard CW Johnson DJ Johnson Westerman Grivna	12/01/2015 9,202,720
DIV of (PT-198) Apparatus for Plasma Dicing a Semi-conductor Wafer - ESC	Martinez Pays-Volard CW Johnson DJ Johnson Westerman Grivna	05/21/2019 10,297,427
DIV of (PT-198) Apparatus for Plasma Dicing a Semi-conductor Wafer - (TDM & Cleaning Step)	Martinez Pays-Volard CW Johnson DJ Johnson Westerman Grivna	02/07/2017 9,564,366
CIP of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Tape Under Tension & Multiple Wafer	Gauldin CW Johnson DJ Johnson Martinez Pays-Volard Westerman Grivna	02/03/2015 8,946,058
Reissue of (PT-199) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Tape Under Tension & Multiple Wafer	Gauldin CW Johnson DJ Johnson Martinez Pays-Volard Westerman Grivna	03/14/2017 RE46339

CIP of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - large area ESC Details with cover ring	Martinez Pays-Volard CW Johnson DJ Johnson Westerman Grivna	06/30/2015 9,070,760
DIV of (PT-201) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - lift mechanism engaging a bottom surface of the work piece	Martinez Pays-Volard CW Johnson DJ Johnson Westerman Grivna	11/15/2016 9,496,177
DIV of (PT-201) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - ICP screen details	Pays-Volard Martinez CW Johnson DJ Johnson Westerman Grivna	08/11/2015 9,105,705
DIV of (PT-205) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - 13.56MHz SOI & mechanical partition	Pays-Volard Martinez CW Johnson DJ Johnson Westerman Grivna	02/25/2020 10,573,557
CIP of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Perforated Cover Ring, Multi-Wafer Cover Ring & PCM Fills	Geerpuram Pays-Volard Martinez CW Johnson DJ Johnson Westerman	04/08/2014 8,691,702
CIP of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Dicing Assist Feature	Lazerand Pays-Volard Martinez CW Johnson Westerman Grivna	05/17/2016 9,343,365
DIV of (PT-206) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Perforated Cover Ring, Multi-Wafer Cover Ring & PCM Fills	Geerpuram Pays-Volard Martinez CW Johnson DJ Johnson Westerman	12/01/2015 9,202,721

CIP of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - intermediate ring with cover ring	Gauldin Geerpuram Mackenzie Lazerand Pays-Volard Martinez Westerman Grivna Doub	07/14/2015 9,082,839
DIV of (PT-217) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - intermediate ring without cover ring	Gauldin Geerpuram Mackenzie Lazerand Pays-Volard Martinez Westerman Grivna Doub	12/01/2015 9,202,737
DIV of (PT-241) Device for Treating an Object with Plasma	Baujon Guidotti Pilloux Rabinzohn Richard Segers Girault	07/27/2021 11,075,057
Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - GaAs	Chiang Westerman	04/23/2019 10,269,641
DIV filing of (PT243) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - GaAs	Chiang Westerman	10/27/2020 10,818,552
Powered Anode for Ion Source for DLC and Reactive Processes	Hegde Lee	01/09/2018 9,865,436
Wafer Stage for Symmetric Wafer Processing	Hegde Lee Goglia	01/09/2018 9,863,036
Grid Assemblies for Use in Ion Beam Etching Systems and Methods of Utilizing the Grid Assemblies	Hegde	04/22/2014 8,703,001
DIV of (PT-201.1) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - large area ESC Details without cover ring	Martinez Pays-Volard CW Johnson DJ Johnson Westerman Grivna	03/06/2018 9,911,654
DIV of (PT-263) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - ICP screen adjustment	Martinez Pays-Volard CW Johnson DJ Johnson Westerman Grivna	08/11/2020 10,741,447

DIV of (PT-201.2) Method and Apparatus for Plasma Dicing a Semiconductor Wafer - Frame & Cover Ring (Tape & Frame Exposed)	Martinez Pays-Volard CW Johnson DJ Johnson Westerman Grivna	07/18/2017 9,711,406
Method for Dicing Die Attach Film - VHF	Notarianni Lea Westerman	03/09/2021 10,943,825
METHOD FOR REMOVING A METAL DEPOSIT PLACED ON A SURFACE IN A CHAMBER	Vitiello Delcarri Piallat	04/02/2019 10,246,781
METHOD FOR REMOVING A METAL DEPOSIT ARRANGED ON A SURFACE IN A CHAMBER	Vitiello Piallat	09/07/2021 11,114,340
METHOD FOR PRODUCING AN INTERCONNECTION COMPRISING A VIA EXTENDING THROUGH A SUBSTRATE	Vitiello Piallat	09/08/2020 10,767,257
DEVICE AND PROCESS FOR CHEMICAL VAPOR PHASE TREATMENT	BOREAN DELCARRI	03/03/2015 US8967081
CHEMICAL VAPOR DEPOSITION DEVICE	NAL BOREAN VITIELLO	10/03/2017 9,777,374
Embedded attenuated phase shift mask and method of making embedded attenuated phase shift mask	Westerman Constantine	4/8/2003 6,544,696